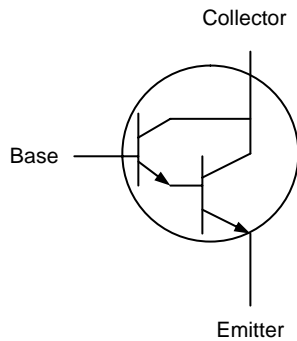


NPN Silicon Darlington Transistor


1. Collector 2. Base 3. Emitter

 TO-92 Plastic Package
 Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	40	V
Collector Emitter Voltage	V_{CES}	30	V
Emitter Base Voltage	V_{EBO}	10	V
Collector Current	I_C	500	mA
Total Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_S	- 55 to + 150	$^\circ\text{C}$

Characteristics ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 2\text{ V}$, $I_C = 20\text{ mA}$	h_{FE}	30,000	-	-	-
Collector Saturation Voltage at $I_C = 100\text{ mA}$, $I_B = 0.1\text{ mA}$	V_{CEsat}	-	-	1	V
Base Emitter On Voltage at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$	$V_{BE(on)}$	-	-	1.4	V
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	40	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 2\text{ mA}$	$V_{(BR)CES}$	30	-	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	10	-	-	V
Collector Cutoff Current at $V_{CE} = 30\text{ V}$	I_{CES}	-	-	500	nA
Collector Cutoff Current at $V_{CB} = 30\text{ V}$	I_{CBO}	-	-	100	nA
Emitter Cutoff Current at $V_{EB} = 10\text{ V}$	I_{EBO}	-	-	100	nA
Current-Gain-Bandwidth Product at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	-	200	-	MHz

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